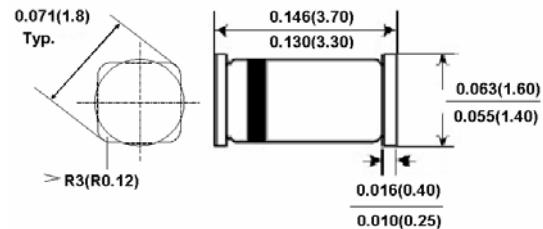


QUADRO MINI MELF



Features

- ◊ Fast switching device ($T_{RR} < 4.0\text{nS}$)
- ◊ Quadro Mini-MELF package
- ◊ Surface device type mounting
- ◊ Hermetically sealed glass
- ◊ Compression bonded construction
- ◊ All external surfaces are corrosion resistant and leads are readily solderable
- ◊ RoHS compliant
- ◊ Matte Tin (Sn) lead finish
- ◊ 1st band indicates cathode

Dimensions in inches and (millimeters)

Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

Maximum Ratings

Type Number	Symbol	Value	Units
Power Dissipation	Pd	500	mW
Working Inverse Voltage	WIV	75	V
Non-repetitive Peak Forward Current	IFM	450	mA
Average Rectified Current	Io	150	mA
Peak Forward Surge Current	I _{SURGE}	2	A
Operating Junction Temperature	T _J	175	°C
Storage Temperature Range	T _{STG}	-65 to + 200	°C

Electrical Characteristics

Type Number	Symbol	Min	Max	Units
Breakdown Voltage IR=100uA IR=5uA	B _V	100 75		V
Forward Voltage LS4448, LS914B IF=5.0mA LS4148 IF= 10mA LS4448, LS914B IF =100mA	V _F	0.62	0.72 1.0 1.0	V
Reverse Leakage Current VR=20V VR=75V	I _R		25 5	nA uA
Junction Capacitance VR=0, f=1.0MHz	C _j	-	4.0	pF
Reverse Recovery Time (Note 1)	trr	-	4.0	nS

Notes: 1. Reverse Recovery Test Conditions: I_F=I_R=10mA, R_L=100Ω, I_{RR}=1mA

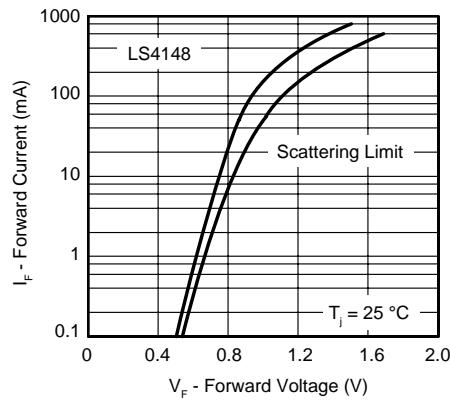
RATINGS AND CHARACTERISTIC CURVES (LS4448/LS4148/LS914B)


Figure 1. Forward Current vs. Forward Voltage

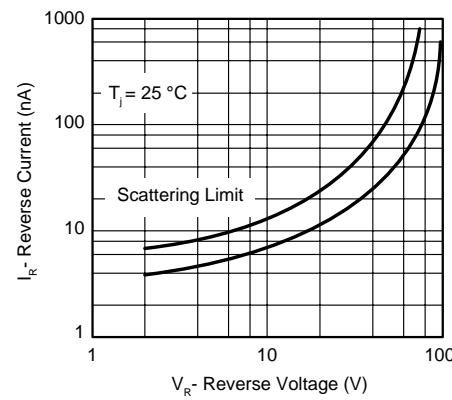


Figure 3. Reverse Current vs. Reverse Voltage

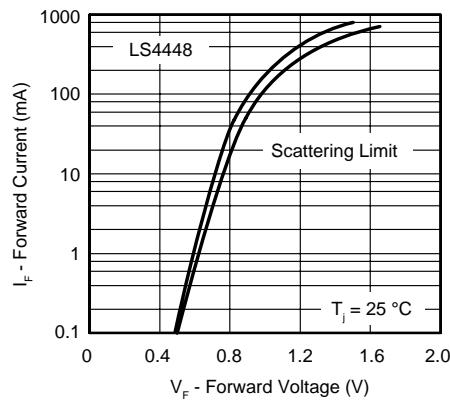


Figure 2. Forward Current vs. Forward Voltage

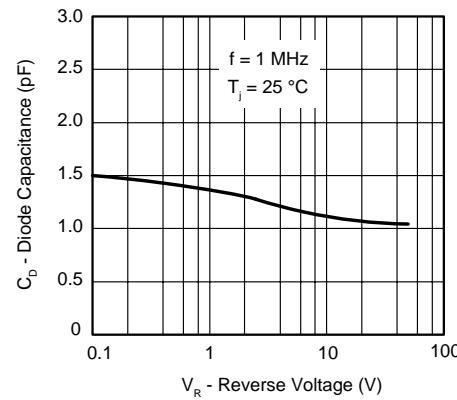


Figure 4. Diode Capacitance vs. Reverse Voltage